





#### **60V P-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub> T <sub>A</sub> = 25°C		
-60V	125mΩ @ V <sub>GS</sub> = -10V	-6.6A		
	190mΩ @ V <sub>GS</sub> = -4.5V	-5.3A		

### **Description and Applications**

This new generation MOSFET has been designed to minimize the onstate resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- DC-DC Converters
- · Power management functions

#### **Features and Benefits**

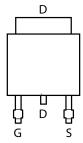
- · Low on-resistance
- Fast switching speed
- "Green" component and RoHS compliant (Note 1)

#### **Mechanical Data**

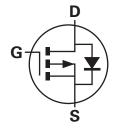
- Case: TO252-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)



Top View



Pin Out -Top View



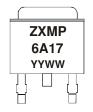
Equivalent Circuit

#### Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel	
ZXMP6A17KTC	See Below	13	16	2,500	

Note: 1. Diodes, Inc. defines "Green" products as those which are Eu RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

# **Marking Information**



ZXMP = Product Type Marking Code, Line 1 6A17 = Product Type Marking Code, Line 2 YYWW = Date Code Marking YY = Year (ex: 09 = 2009) WW = Week (01-52)





### Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Cha	racteristic		Symbol Value		Unit	
Drain-Source voltage			V <sub>DSS</sub>	-60	V	
Gate-Source voltage			$V_{GS}$	±20	V	
		(Note 3)	I <sub>D</sub>	6.6		
Continuous Drain current	$V_{GS} = 10V$	T <sub>A</sub> =70°C (Note 3)		5.3	Α	
		(Note 2)		4.4		
Pulsed Drain current V <sub>GS</sub> = 10V (No		(Note 4)	I <sub>DM</sub>	20.3	Α	
Continuous Source current (Body diode) (Note 3)		Is	9.3	Α		
Pulsed Source current (Body diode) (Note 4)			I <sub>SM</sub>	20.3	Α	

# Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol Value		Unit		
	(Note 2)		4.17 33.3		
Power dissipation Linear derating factor	(Note 3)	P <sub>D</sub>	9.25 74.0	W mW/°C	
	(Note 5)		2.11 16.8		
	(Note 2)		30.0		
Thermal Resistance, Junction to Ambient	(Note 3)	$R_{ heta JA}$	13.5	20.44	
	(Note 5)		59.1	°C/W	
Thermal Resistance, Junction to Lead (Note 6)		$R_{ heta JL}$	2.41		
Operating and storage temperature range		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C	

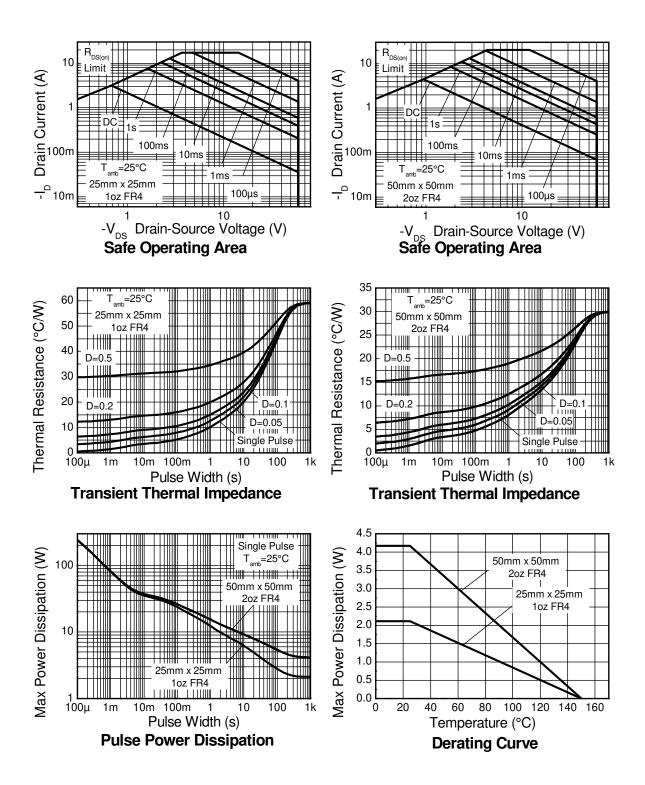
Notes:

- 2. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 3. Same as note 2, except the device is measured at  $t \le 10$  sec.
- Same as note 2, except the device is pulsed with D = 0.02 and pulse width 300 μs. The pulse current is limited by the maximum junction temperature.
  For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Thermal resistance from junction to solder-point (at the end of the drain lead).





#### **Thermal Characteristics**







# Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS	OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	_	_	٧	$I_D = -250 \mu A, V_{GS} = 0 V$		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-0.5	μА	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V		
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS}$ = ±20V, $V_{DS}$ = 0V		
ON CHARACTERISTICS								
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	_	_	٧	$I_{D}$ = -250 $\mu$ A, $V_{DS}$ = $V_{GS}$		
Static Drain-Source On-Resistance (Note 7)	Dag (a)			0.125	Ω	$V_{GS}$ = -10V, $I_{D}$ = -2.3A		
Static Drain-Source Off-Resistance (Note 7)	R <sub>DS</sub> (ON)	_		0.190	\$2	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1.9A		
Forward Transconductance (Notes 7 & 8)	9 <sub>fs</sub>	_	4.7	_	S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -2.2A		
Diode Forward Voltage (Note 7)	$V_{SD}$	_	-0.85	-0.95	V	I <sub>S</sub> = -2A, V <sub>GS</sub> = 0V		
Reverse recovery time (Note 8)	t <sub>rr</sub>		25.1	_	ns	1 74 11/14 1004/		
Reverse recovery charge (Note 8)	Q <sub>rr</sub>	_	27.2	_	nC	-I <sub>S</sub> = -1.7A, di/dt= 100A/μs		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	C <sub>iss</sub>	_	637	_	pF	V 997 V 97		
Output Capacitance	Coss	_	70	_	pF	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V f= 1MHz		
Reverse Transfer Capacitance	Crss	_	53	_	pF	1- 11/11/12		
Total Gate Charge	$Q_g$	_	9.0	_	nC	V <sub>GS</sub> = -4.5V		
Total Gate Charge	Qg	_	17.7	_	nC	V <sub>DS</sub> = -30V		
Gate-Source Charge	Qgs	_	1.6	_	nC	V <sub>GS</sub> = -10V		
Gate-Drain Charge	$Q_{gd}$	_	4.4	_	nC			
Turn-On Delay Time (Note 9)	t <sub>D(on)</sub>	_	2.6	_	ns			
Turn-On Rise Time (Note 9)	t <sub>r</sub>	_	3.4	_	ns	V <sub>DD</sub> = -30V, V <sub>GS</sub> = -10V		
Turn-Off Delay Time (Note 9)	t <sub>D(off)</sub>	_	26.2	_	ns	$I_{D}\text{= -1A, }R_{G}\cong6.0\Omega$		
Turn-Off Fall Time (Note 9)	t <sub>f</sub>	_	11.3	_	ns			

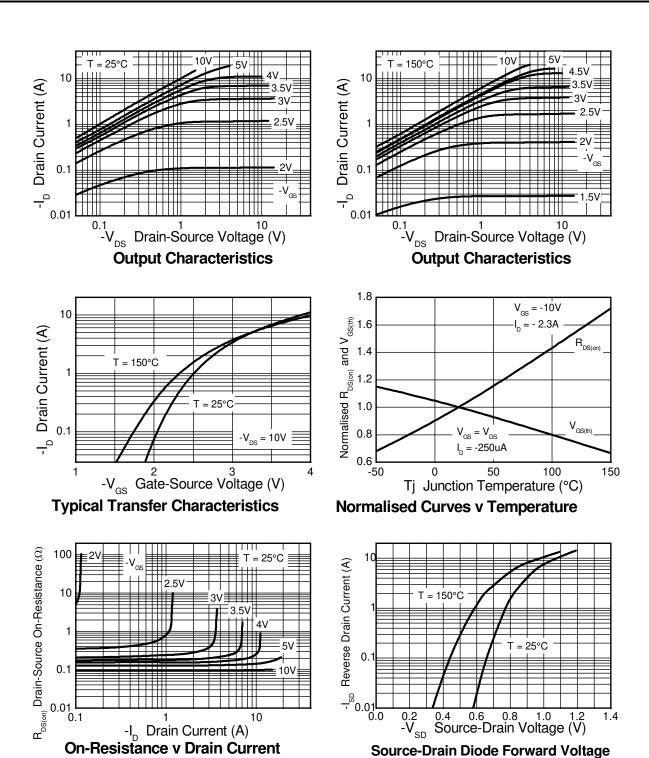
Notes:

- Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%
  For design aid only, not subject to production testing.
  Switching characteristics are independent of operating junction temperatures.





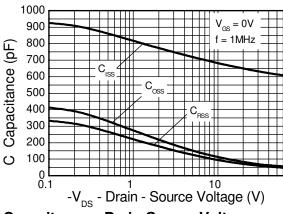
# **Typical Characteristics**



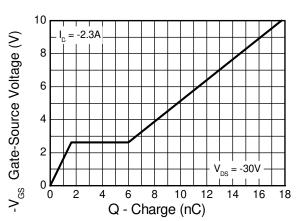




## **Typical Characteristics - continued**

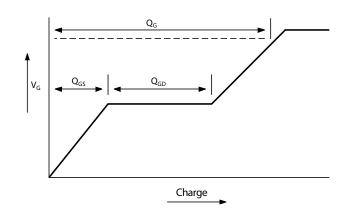


Capacitance v Drain-Source Voltage

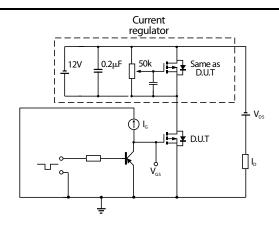


**Gate-Source Voltage v Gate Charge** 

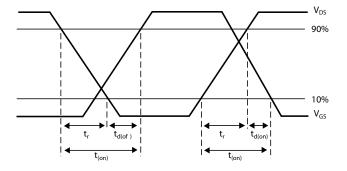
#### **Test Circuits**



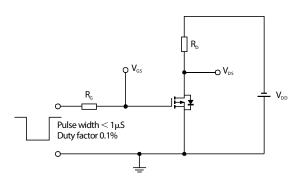
Basic gate charge waveform



Gate charge test circuit



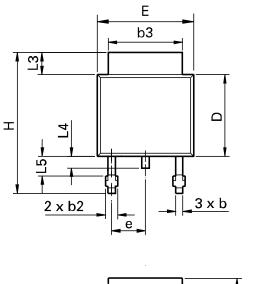
Switching time waveforms

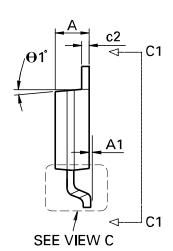


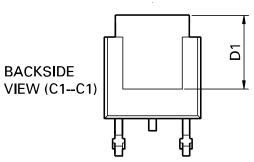
Switching time test circuit

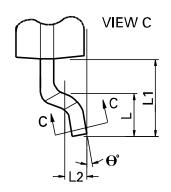


# **Package Outline Dimensions**





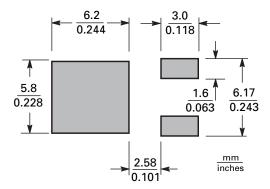




DIM	DIM Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
Α	0.086	0.094	2.18	2.39	е	0.090 BSC		2.29 BSC	
<b>A</b> 1	-	0.005	-	0.127	Н	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
С	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	θ1°	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	θ°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-



## Suggested Pad Layout



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